1. (Amended) A quartz thin film made by depositing at least one silicon alkoxide selected from the group consisting of tetramethoxysilane, tetraethoxysilane, tetrapropoxysilalne and tetrabutoxysilane on a substrate under atmospheric pressure.

2. (Amended) A quartz film as claimed in claim 1, which is a quartz epitaxial thin film.

Please add the following claims:

--8. The article of Claim 2 wherein said epitaxial layer is characterized by an X-ray diffraction profile exhibiting a diffraction peak at 2θ=50.6°.

9. The article of Claim 2, which further comprises a third layer which is a buffer layer which is disposed between said substrate and said crystal thin film.

10. The article of Claim 9,wherein the buffer layer is GaN or ZnO

11. The article of Claim 9, wherein the buffer layer comprises amorphous material

12. The article of Claim 9, wherein the buffer layer comprises amorphous crystal

13. An article of manufacture selected from the group consisting of vibrators, oscillator, high frequency filter surface acoustic wave element, optical waveguide, semiconductor substrate wherein the manufactured article comprises the article of Claim 1.

14. An article comprising a quartz thin film grown on a substrate under atmospheric pressure,

wherein the quartz thin film comprises a deposit formed from at least one silicon alkoxide selected from the group consisting of tetramethoxysilane, tetraethoxysilane, tetrapropoxysilalne and tetrabutoxysilane; and

wherein the substrate comprises a material selected from the group consisting of sapphire, silicon, and GaAs. --

15. The article of Claim 14, which further comprises a third layer which is a buffer layer which is disposed between said substrate and said crystal thin film.

16. The article of Claim 15, wherein the buffer layer is GaN or ZnO.

17. The article of Claim 16, wherein the buffer layer comprise amorphous material.

18. A article of Claim 14, wherein the substrate comprises sapphire.

19. The article of Claim 14, wherein said epitaxial layer is characterized by an X-ray diffraction profile exhibiting a diffraction peak at $2\theta=50.6^{\circ}$.

20. An article of manufacture selected from the group consisting of vibrators, oscillator, high frequency filter surface acoustic wave element, optical waveguide, semiconductor substrate wherein the manufactured article comprises the article of Claim 14. --

REMARKS

Reconsideration of the outstanding Office Action is respectfully solicited. (A marked-up version of amendments of Claims 1 and 2 is attached.)

Applicants enclose herewith two attachments including a clean copy and a marked up version of a substitute specification. This presentation is to conform the specification to the drawings. In the drawings the word quartz is used; please see Figure 6. However in translation of the Japanese language specification, the Japanese word for "quartz" may also refer to crystal. This is evidenced by comparing the terms on Figure 6 referring to quartz to the terms in the specification describing Figure 6 which refers to employs the word 'crystal' Example 2, at page 15 line 8 thereof. Amorphous silicon dioxide and single crystalline silicon dioxide (quartz) can be represented by the same chemical formula "SiO2". However, single crystalline silicon